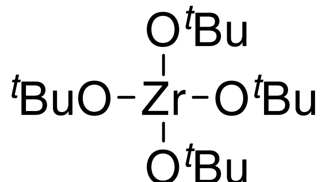
Strem Chemicals, Inc. **strem.com**

Catalog # 40-1749 Zirconium(IV) t-butoxide, 99%



Thermal Behavior:

- Melting point: 2-3°C
- Boiling point: 56°C at 0.1 Torr [1]
- Vapor Pressure: 5 Torr at 90°C [2-3]

Technical Notes:

1. ALD/CVD precursor for Zr thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
ZrO_2	ALD	-	2 Torr	H_2O	80-140°C	4
	MLD	30°C	0.3 Torr	H_2O	170°C	5
	UV-ALD	35°C	2 Torr	H_2O	RT	6
	photo-ALD	RT	7.5 Torr		150-245°C	7
	PE-ALD	90°C	1 Torr	$^{PL}O_2$	250°C	8
	ALD	50°C	0.5-1 Torr	H_2O; O_2; N_2O	150-300°C	9
	ALD	70-80°C	1 Torr	^{PL}Ar; $^{PL}O_2$	100°C	10
ZrF	ALD	65°C	1 Torr	HF·Py	150°C	11

References:

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